



Shantou Huashan Electronic Devices Co., Ltd.

NPN SILICON TRANSISTOR

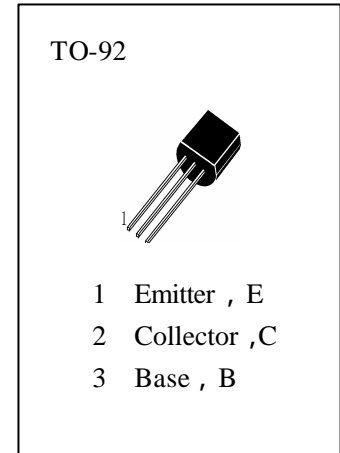
H380TM

APPLICATIONS

High Frequency Amplifier Application

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	—Storage Temperature.....	-55~150
T_j	—Junction Temperature.....	150
P_C	—Collector Dissipation.....	300mW
V_{CBO}	—Collector-Base Voltage.....	35V
V_{CEO}	—Collector-Emitter Voltage.....	30V
V_{EBO}	—Emitter-Base Voltage.....	4V
I_C	—Collector Current.....	50mA
I_E	—Emitter Current.....	50mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	35			V	$I_C=100 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	30			V	$I_C=1 mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	4			V	$I_E=100 \mu A, I_C=0$
HFE	DC Current Gain	40		240		$V_{CE}=12V, I_C=2mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.4	V	$I_C=10mA, I_B=1 mA$
$V_{BE(sat)}$	Base-Emitter Voltage			1.0	V	$I_C=10mA, I_B=1 mA$
ICBO	Collector Cut-off Current			0.1	μA	$V_{CB}=35V, I_E=0$
IEBO	Emitter Cut-off Current			1.0	μA	$V_{EB}=4V, I_C=0$
ft	Current Gain-Bandwidth Product	100		400	MHz	$V_{CE}=10V, I_C=1 mA$
Cob	Output Capacitance	1.4	2.0	3.2	pF	$V_{CB}=10V, I_E=0, f=1MHz$

hFE Classification

R	O	Y
40—80	70—140	120—240